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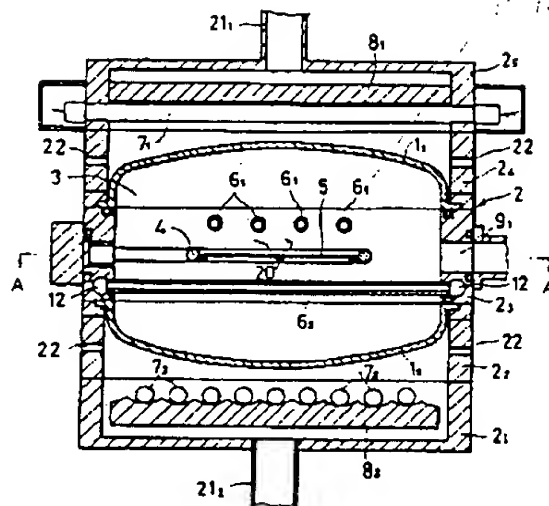
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APPLICANT : SHINKU RIKO KK;

INVENTOR : ICHIHASHI MASAHIKO;

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TITLE : RAPID HEATING AND COOLING
DEVICE FOR SEMICONDUCTOR
WAFER TREATMENT



ABSTRACT : PURPOSE: To rapidly heat up or cool down wafers as well as to maintain the wafers at a uniform temperature by a method wherein two infrared ray lamps, orthogonally intersecting with each other opposing to a pair of bell jars, are arranged and two nozzles to be used for blowing of cooling gas, crossing at right angle with each other, are provided on one surface and other surface of the wafer arranged in a chamber.

CONSTITUTION: When infrared ray lamps 7_1 and 7_2 are lighted up, as a chamber 3 has a short distance between the upper and the lower sides and the infrared lamps 7_1 and 7_2 are arranged in close vicinity to the upper and the lower sides of a wafer 5, the wafer is heated up quickly. Also, as the infrared ray lamps 7_1 and 7_2 are arranged at right angle with each other, the wafer 5 can be heated up to a uniform temperature on the whole surface, and also the temperature distribution of the wafer 5 can be controlled two-dimensionally by regulating the power applied to the infrared ray lamps 7_1 and 7_2 . When a cooling control device 14 is operated and the cooling gas such as helium and the like is blown against the upper and the lower surfaces of the wafer from nozzles 6_1 and 6_2 , the whole surface of the wafer 5 can be cooled uniformly, because the nozzles 6_1 and 6_2 are crossed at right angle with each other.

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